



Attorney's Docket No.: 01977/093002/US3164D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hisashi Ohtani, et al.

Art Unit : 2815

Serial No.: 09/379,702

Examiner : Eugene Lee

Filed : August 24, 1999

Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

Commissioner for Patents

Washington, D.C. 20231

AMENDMENT

Sir:

In response to the Official Action dated November 13, 2000, Paper No, 6, in the above-referenced application, please amend the above-identified application as follows.

In the Specification:

Please replace the paragraph beginning at page 9, line 7 with the following rewritten paragraph:

C  
--Measurements with an AFM (Atomic Force Microscopy) have revealed that where no capping layer existed as in the prior art techniques, the sizes of the ridges were about 500 Å, and that

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I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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